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Substitute for form 1449/PTO		Complete if Known			
		Application Number	10/8/1729		
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INFORMATION DISCLOSURE				First Named Inventor	Ravishankar Sundaresan
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(Use as many sheets as necessary)				Examiner Name	
Sheet	1	of	3	Attorney Docket Number	91-C-134D2 (STMI01-00098)

			U. S. PATEN	T DOCUMENTS	
Examiner Initials*	Cite No.1	Document Number  Number-Kind Code <sup>2 (f known)</sup>	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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		FORE	IGN PATENT DOCL	JMENTS		
Examiner Initials*	Cite No.1	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages	Π
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Attorney Docket Number 91-C-134D2 (STMI01-0

			U. S. PATENT (		
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant
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